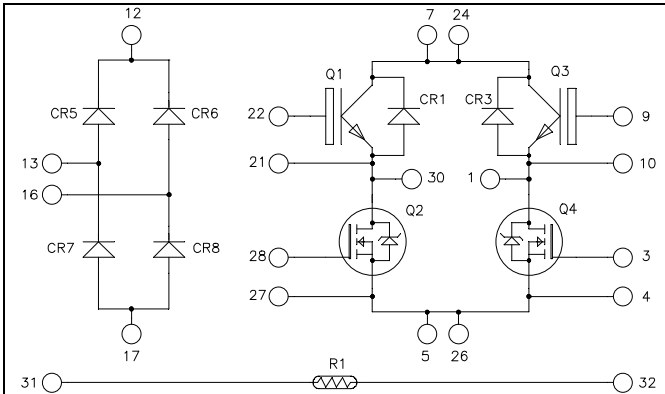
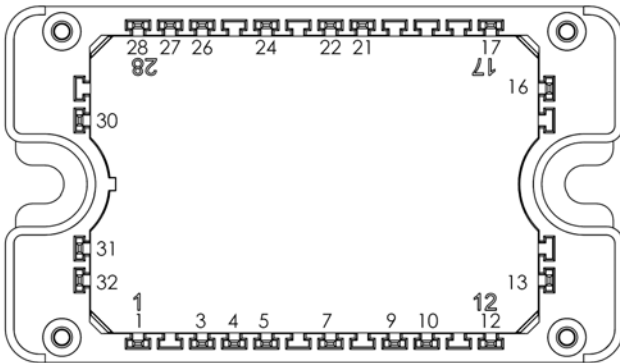


**Full bridge + rectifier bridge
CoolMOS™ & Trench + Field Stop IGBT3
Power Module**



Top switches : Trench + Field Stop IGBT3
Bottom switches : CoolMOS™



All multiple inputs and outputs must be shorted together
7/24 ; 5/26

Trench & Field Stop IGBT3 Q1, Q3:
 $V_{CES} = 600V$; $I_C = 50A$ @ $T_c = 80^\circ C$

CoolMOS™ Q2, Q4:
 $V_{DSS} = 600V$

$R_{DSon} = 45m\Omega$ max @ $T_j = 25^\circ C$

Application

- Solar converter

Features

- **Q2, Q4 CoolMOS™**
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
- **Q1, Q3 Trench & Field Stop IGBT3**
 - Low voltage drop
 - Switching frequency up to 20 kHz
 - RBSOA & SCSOA rated
 - Low tail current

- Very low stray inductance
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Optimized conduction & switching losses
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_c of V_{CEsat}
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

1. Top switches

1.1 Top Trench + Field Stop IGBT3 characteristics (per IGBT)

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 50A$		1.5	1.9	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu A$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		3150		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		200		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		95		
Q_G	Gate charge	$V_{GE} = \pm 15V, I_C = 50A$ $V_{CE} = 300V$		0.5		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{off}	Turn-off Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$ $R_G = 8.2\Omega$		1.35		mJ
		$T_j = 25^\circ C$		1.75		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 360V$ $t_p \leq 6\mu s; T_j = 150^\circ C$		250		A
R_{thJC}	Junction to Case Thermal resistance				0.85	$^\circ C/W$

1.2 Top diode characteristics (CR1, CR3) (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C			25	μA
			T _j = 125°C			500	
I _F	DC Forward Current	T _c = 80°C			25		A
V _F	Diode Forward Voltage	I _F = 25A			1.8	2.2	V
		I _F = 50A			2.2		
		I _F = 25A	T _j = 125°C		1.6		
t _{rr}	Reverse Recovery Time	I _F = 25A V _R = 400V di/dt = 200A/μs	T _j = 25°C		30		ns
			T _j = 125°C		175		
Q _{rr}	Reverse Recovery Charge	I _F = 25A V _R = 400V di/dt = 200A/μs	T _j = 25°C		55		nC
			T _j = 125°C		485		
R _{thJC}	Junction to Case Thermal resistance					1.4	°C/W

2. Bottom switches
2.1 Bottom CoolMOS™ characteristics (Per CoolMOS™)
Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage	600	V
I _D	Continuous Drain Current	T _c = 25°C	49
		T _c = 80°C	38
I _{DM}	Pulsed Drain current	130	
V _{GS}	Gate - Source Voltage	±20	V
R _{DS(on)}	Drain - Source ON Resistance	45	mΩ
P _D	Maximum Power Dissipation	T _c = 25°C	250
I _{AR}	Avalanche current (repetitive and non repetitive)	15	A
E _{AR}	Repetitive Avalanche Energy	3	mJ
E _{AS}	Single Pulse Avalanche Energy	1900	

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 600V	T _j = 25°C			250	μA
		V _{GS} = 0V, V _{DS} = 600V	T _j = 125°C			500	
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 24.5A			40	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 3mA		2.1	3	3.9	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0V				100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{iss}	Input Capacitance	V _{GS} = 0V ; V _{DS} = 25V f = 1MHz		7.2		nF
C _{oss}	Output Capacitance			8.5		
Q _g	Total gate Charge	V _{GS} = 10V V _{Bus} = 300V I _D = 49A		150		nC
Q _{gs}	Gate – Source Charge			34		
Q _{gd}	Gate – Drain Charge			51		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) V _{GS} = 10V V _{Bus} = 400V I _D = 49A R _G = 5Ω		21		ns
T _r	Rise Time			30		
T _{d(off)}	Turn-off Delay Time			100		
T _f	Fall Time			45		
E _{on}	Turn-on Switching Energy	Inductive switching @ 25°C V _{GS} = 10V ; V _{Bus} = 400V I _D = 49A ; R _G = 5Ω		675		μJ
E _{off}	Turn-off Switching Energy			520		
E _{on}	Turn-on Switching Energy	Inductive switching @ 125°C V _{GS} = 10V ; V _{Bus} = 400V I _D = 49A ; R _G = 5Ω		1096		μJ
E _{off}	Turn-off Switching Energy			635		
R _{thJC}	Junction to Case Thermal resistance				0.5	°C/W

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _S	Continuous Source current (Body diode)	T _c = 25°C		49		A
		T _c = 80°C		38		
V _{SD}	Diode Forward Voltage	V _{GS} = 0V, I _S = - 49A			1.2	V
dv/dt	Peak Diode Recovery ❶				4	V/ns
t _{rr}	Reverse Recovery Time	I _S = - 49A V _R = 350V di _S /dt = 100A/μs	T _j = 25°C		600	ns
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		17	μC

❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -49A \quad di/dt \leq 100A/\mu s \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ C$$

3. Rectifier bridge (per diode)
Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V _R	Maximum DC reverse Voltage	600	V
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		
I _{F(AV)}	Maximum Average Forward Current	40	A
I _{FSM}	Non-Repetitive Forward Surge Current		
		8.3ms	T _j = 45°C

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _F	Diode Forward Voltage	I _F = 30A		1.8	2.2	V
		I _F = 60A		2.2		
		I _F = 30A	T _j = 125°C		1.5	
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V	T _j = 25°C		250	μA
			T _j = 125°C		500	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F=1A, V_R=30V$ $di/dt = 100A/\mu s$	$T_j = 25^\circ C$		22		ns
t_{rr}	Reverse Recovery Time	$I_F = 30A$ $V_R = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$		25		ns
			$T_j = 125^\circ C$		160		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ C$		35		nC
			$T_j = 125^\circ C$		480		
I_{RRM}	Reverse Recovery Current		$T_j = 25^\circ C$		3		A
		$T_j = 125^\circ C$		6			
t_{rr}	Reverse Recovery Time	$I_F = 30A$ $V_R = 400V$ $di/dt = 1000A/\mu s$	$T_j = 125^\circ C$		85		ns
Q_{rr}	Reverse Recovery Charge				920		μC
I_{RRM}	Reverse Recovery Current				20		A
R_{thJC}	Junction to Case Thermal Resistance					1.2	$^\circ C/W$

4. Thermal and package characteristics
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		50		k Ω
$\Delta R_{25}/R_{25}$			5		%
$B_{25/85}$	$T_{25} = 298.15 K$		3952		K
$\Delta B/B$	$T_C = 100^\circ C$		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

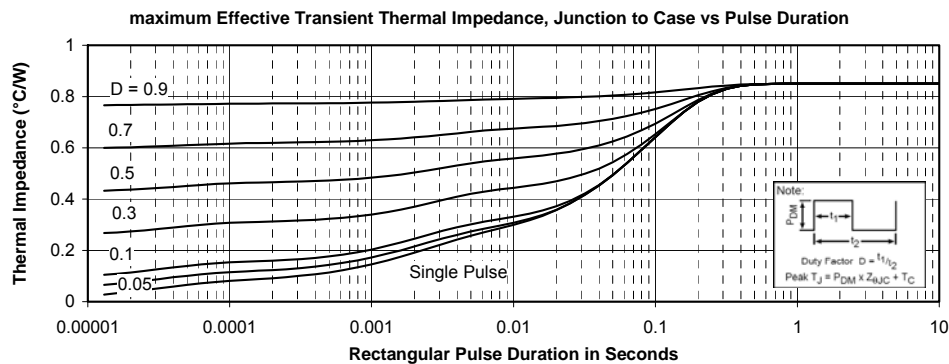
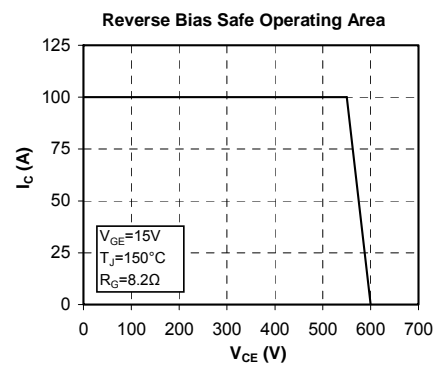
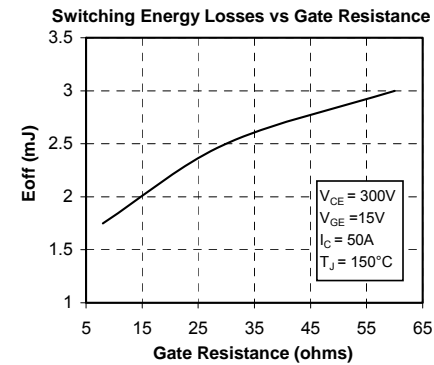
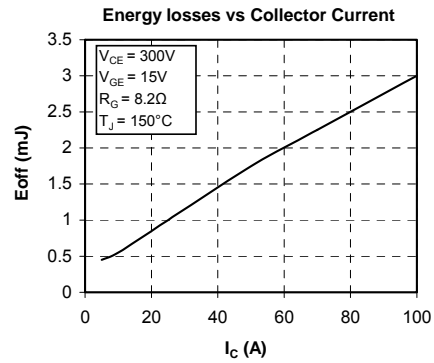
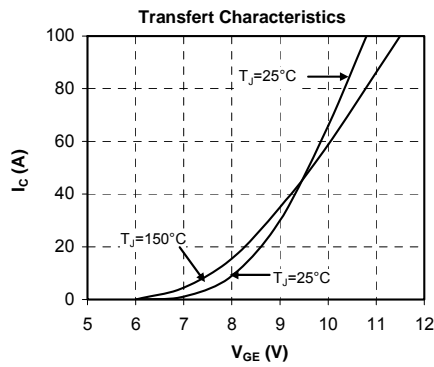
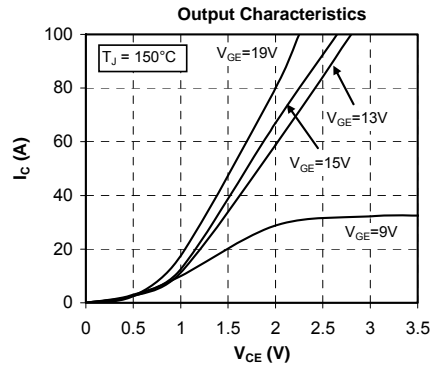
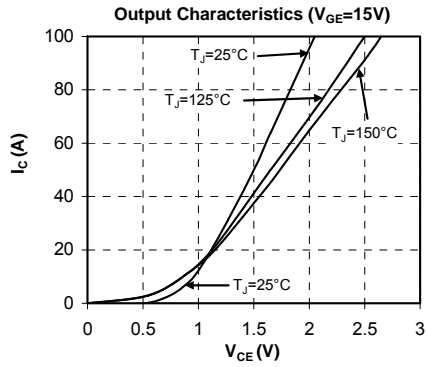
T: Thermistor temperature
 R_T : Thermistor value at T

Package characteristics

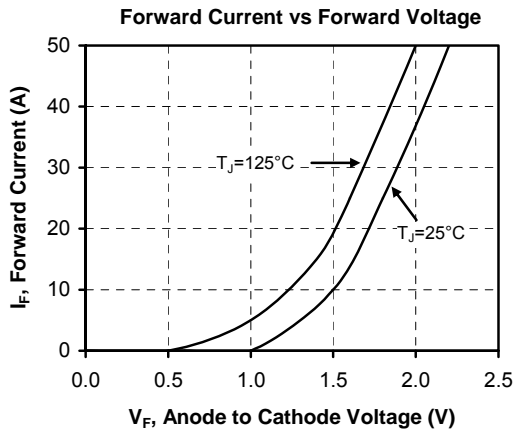
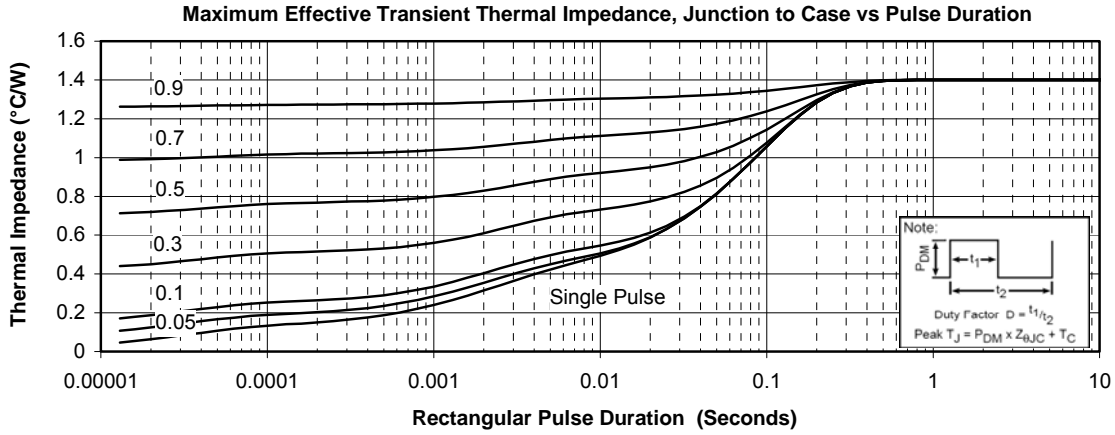
Symbol	Characteristic	Min	Typ	Max	Unit	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	4000			V	
T_j	Operating junction temperature range	-40		175	$^\circ C$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

5. Top switches curves

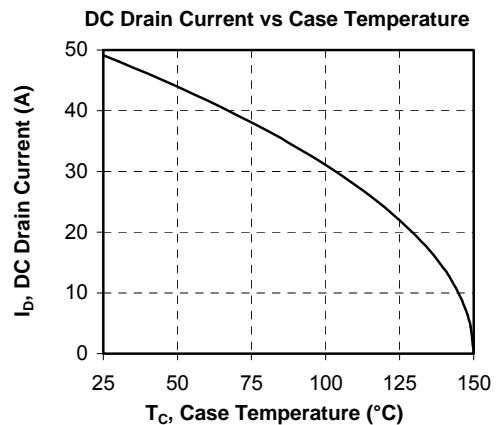
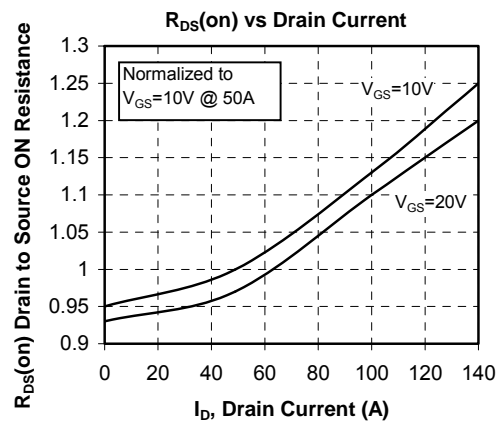
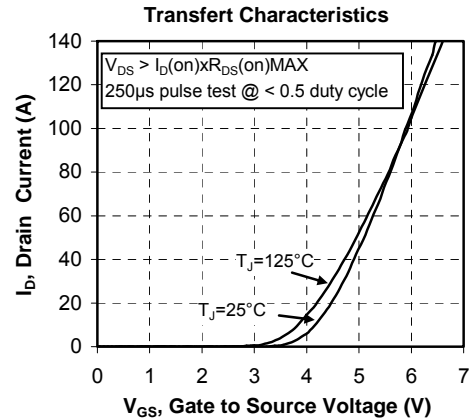
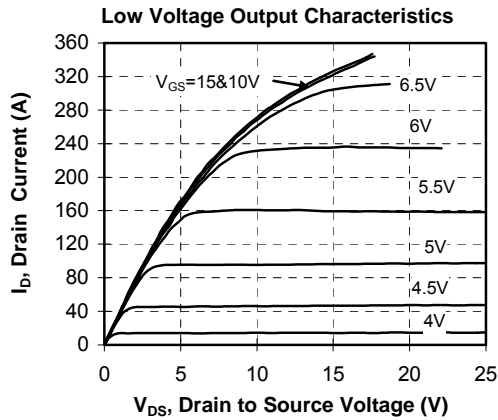
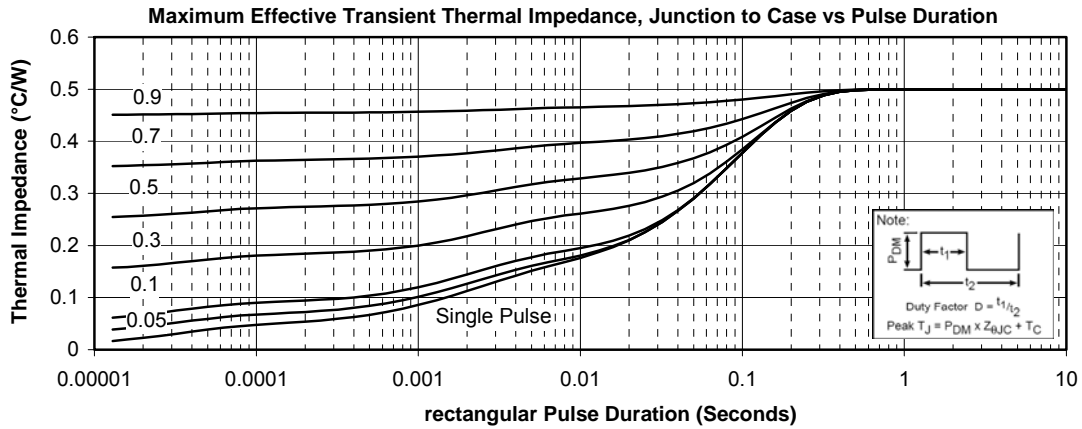
5.1 Top Trench + Field Stop IGBT3 typical performance curves (per IGBT)

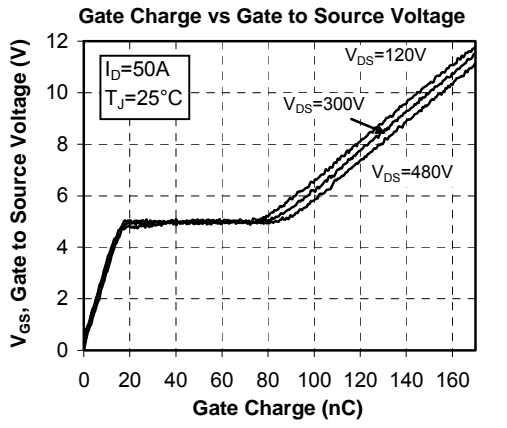
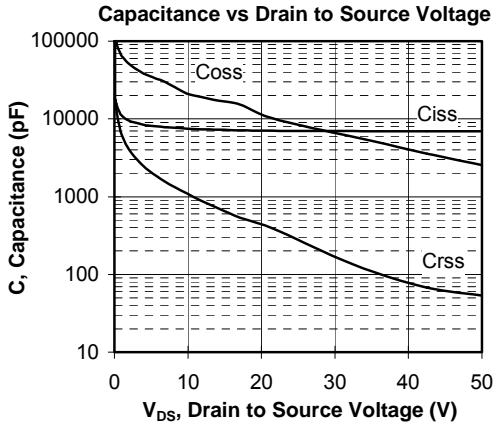
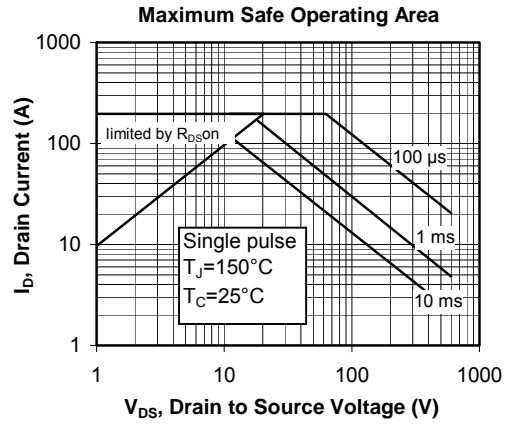
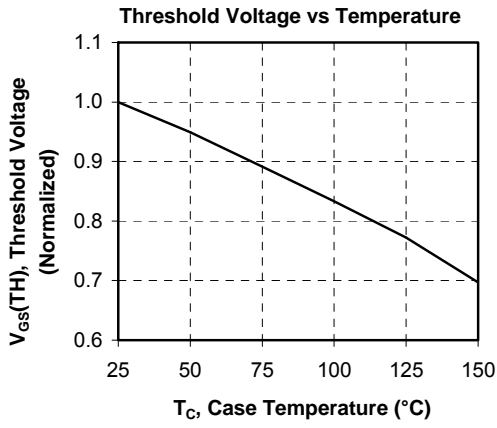
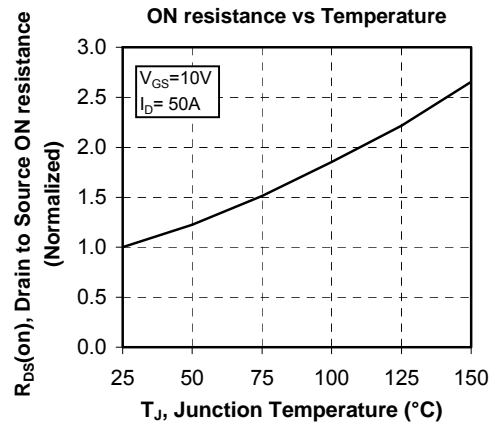
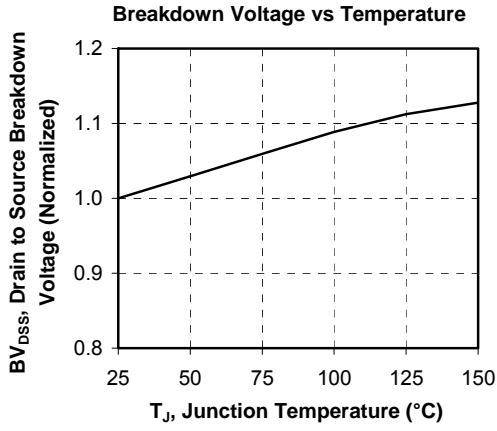


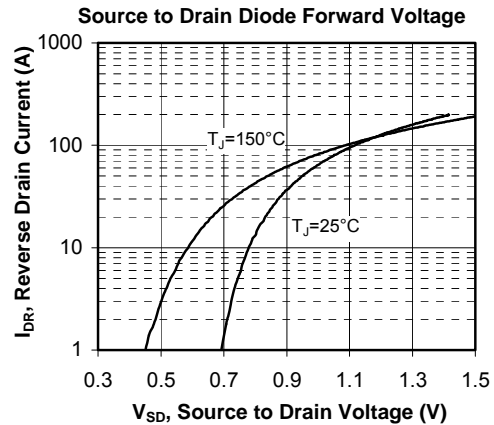
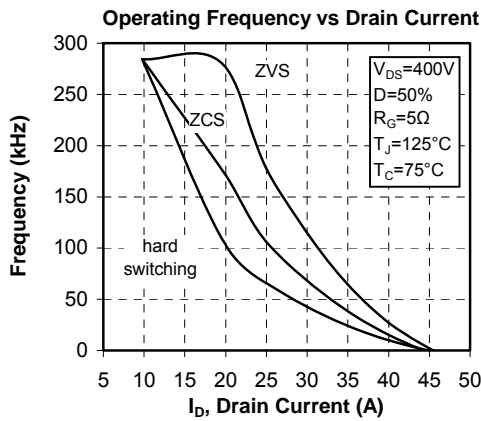
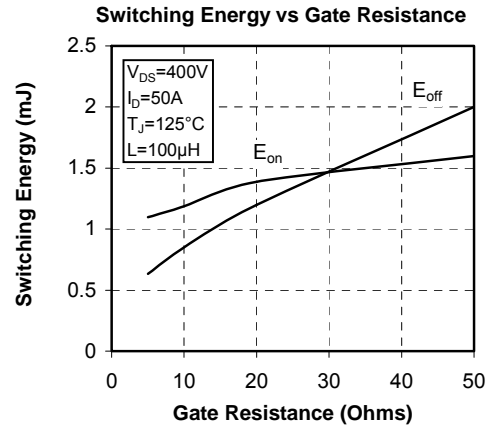
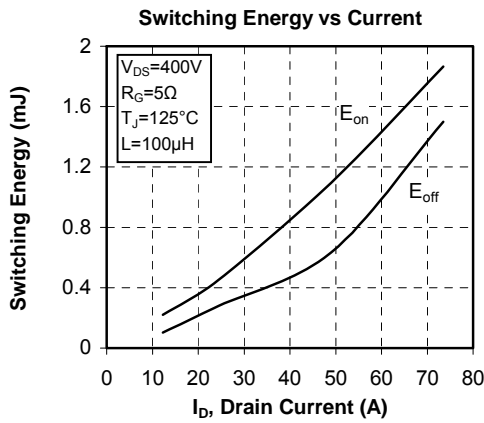
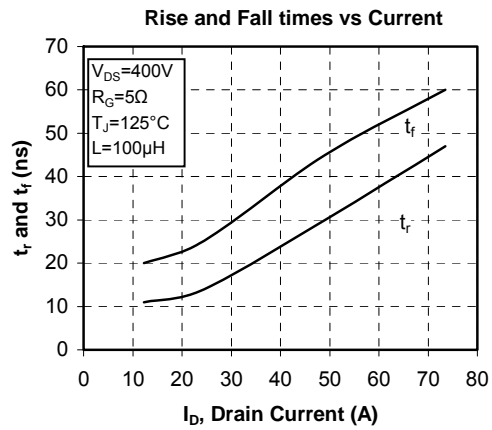
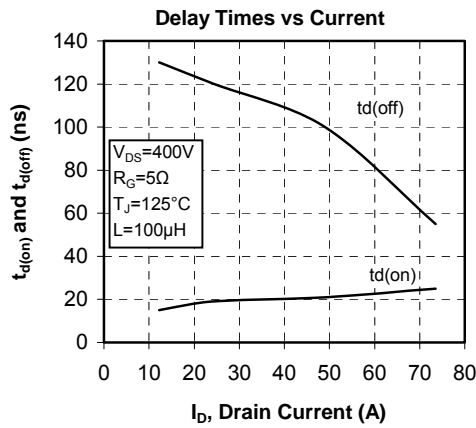
5.2 Top diode characteristics (per diode)



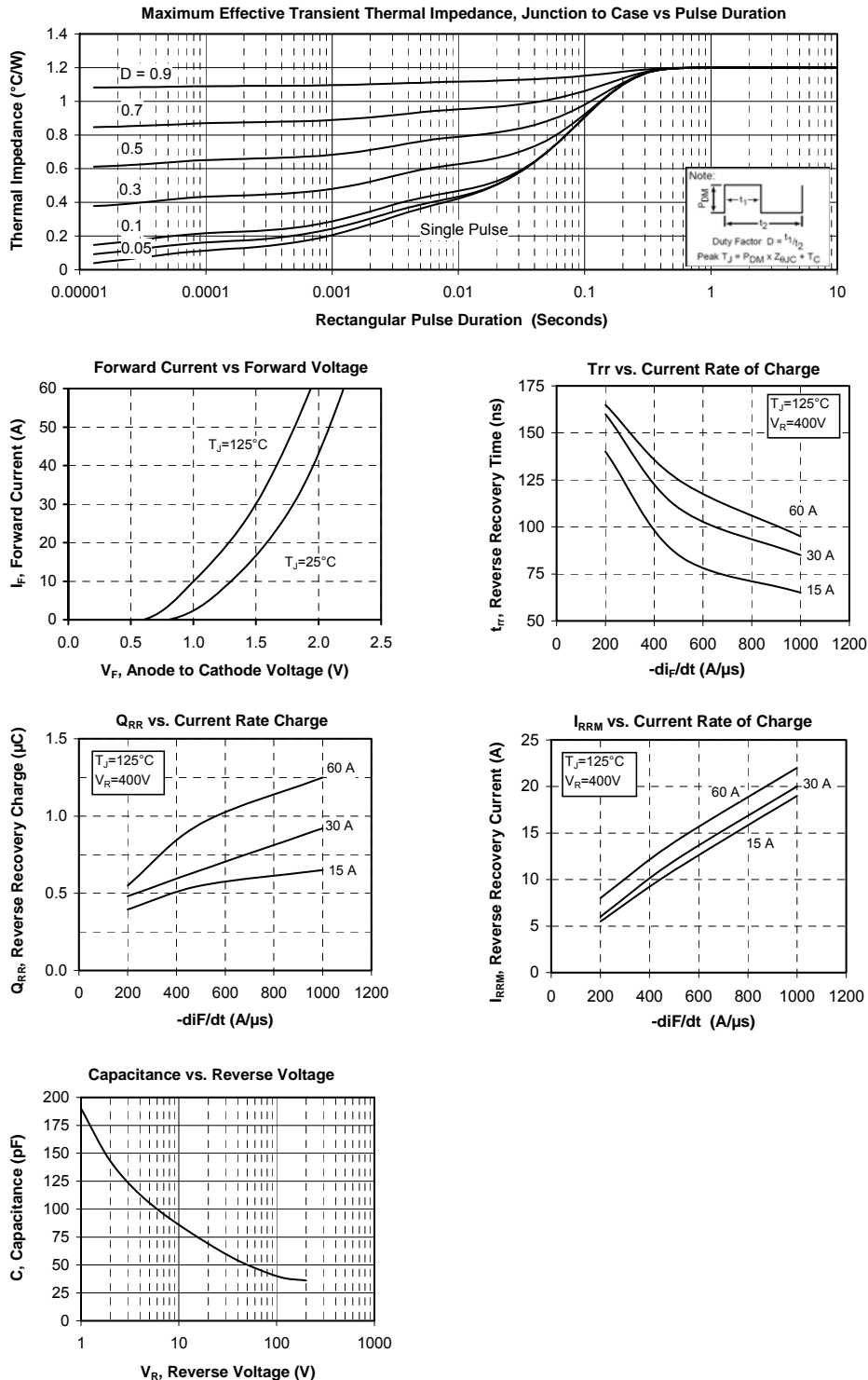
6. Bottom switches curves (per CoolMOST™)







7. Typical rectifier bridge Performance Curve (per diode)



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